Name:

EXAM #3

Closed book, closed notes. Calculators may be used for numeric computations only. All work is to be your own - **show your work** for maximum partial credit.

Data:

Use the following data in all the problems in the Exam:

V_{DD}	1.8V
$\mu_n C_{ox}$	$200 \mu A/V^2$
$\mu_p C_{ox}$	$100 \mu A/V^2$
V _{THN}	0.4V
V _{THP}	0.5V

NMOS Equations

Cutoff region $I_D = 0, V_{GS} < V_{THN}$ Triode (linear) region

 $I_{D} = \mu_{n} C_{ox} \frac{W}{L} \left(\left(V_{GS} - V_{THN} \right) V_{DS} - \frac{V_{DS}^{2}}{2} \right), V_{GS} > V_{THN}, V_{DS} < V_{GS} - V_{THN} \right)$

Saturation region

$$I_{D} = \frac{1}{2} \mu_{n} C_{ox} \frac{W}{L} (V_{GS} - V_{THN})^{2}, V_{GS} > V_{THN}, V_{DS} \ge V_{GS} - V_{THN}$$

Small-signal Parameters

$$g_m = \mu_n C_{ox} \frac{W}{L} \left(V_{GS} - V_{THN} \right) = \sqrt{2\mu_n C_{ox} \frac{W}{L} I_D} = \frac{2I_D}{V_{GS} - V_{THN}}$$
$$r_0 = \frac{1}{\lambda I_D}$$

PMOS Equations

Assuming all positive convention, make the substitutions in the above equations: $\mu_n \rightarrow \mu_p$, $V_{GS} \rightarrow V_{SG}$, $V_{DS} \rightarrow V_{SD}$, and $V_{THN} \rightarrow |V_{THP}|$



1. (25 points) **CMOS Amplifier Design**: Assume that the transconductances of all the transistors in this problem is equal to g_m and the output resistance is r_0 . Also, V_{b1} and V_{b2} are DC bias voltages. Clearly show your work.

(a) (5 points) Find the small-signal gain of the amplifier (in terms of g_m and r_o) shown below.



(b) (10 points) Assume that M_1 and M_2 are in saturation. Using small-signal analysis, find the output resistance (R_0) in the circuit shown below.



(c) (10 points) Using the result from part (b), find the small-signal gain of the amplifier shown below. Compare the answer with the result in part (a).



2. (25 points) Find small-signal voltage gain of the amplifier stages shown below in terms of transistor small-signal parameters g_{m1} , g_{m2} , r_{o1} , r_{o2} , R_s , etc. (Assume that all transistors are in saturation and $\lambda \neq 0$). V_{b1} , V_{b2} , etc., are DC bias voltages. Show your work.











3. (25 points) Design a generated CS amplifier design following the given steps. The amplifier must provide a voltage gain of 4 with a power budget of 2mW while the drop across R_s is equal to 200 mV. The overdrive ($V_{ov}=V_{GS}-V_{THN}$) of the transistor M_1 should be 300mV and the total power consumed in the biasing resistances ($R_1 + R_2$) should be only 5% of the total power. Assume that C_1 is very large. *Use MOSFET data from the first page*.



(a) (4 points) Given the power budget for the transistor M_1 , estimate the value of the bias current (**I**_D).

(b) (4 points) Using part (a), find the value of \mathbf{R}_{s} .

(c) (4 points) For the current, I_D , estimate the W/L ratio of the transistor.

(d) (5 points) Estimate the value of $\mathbf{R}_{\mathbf{D}}$ for the required small-signal gain, $A_v=4$.

(e) (4 points) Find the voltage at the gate of M_1 , (VG)

(f) (4 points) Using the 5% power budget constraint, and the gate voltage (V_G) estimate the value of resistors R_1 and R_2 .

5. (25 points) Consider the amplifier circuit shown below. Assume C_1 and C_2 are very large. Use MOSFET data from the first page.



(a) (10 points) Draw the DC picture (i.e., the equivalent circuit considering only the DC quantities) for the amplifier and find ALL the node voltages in the circuit. Is M₁ biased in saturation?

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(b) (10 points) Draw the AC picture (i.e., the equivalent circuit considering only small-signal quantities) and find the small-signal gain (A_v) and input impedance (R_{in}) of the amplifier.